

# OVERVOLTAGE AND OVERCURRENT PROTECTION IC AND Li+ CHARGER FRONT-END PROTECTION IC

#### **FEATURES**

- Provides Protection for Three Variables:
  - Input Overvoltage, with Rapid Response in  $< 1 \mu s$
  - User-Programmable Overcurrent with Current Limiting
  - Battery Overvoltage
- 30V Maximum Input Voltage
- Supports up to 1.5A Input Current
- Robust Against False Triggering Due to Current Transients
- Thermal Shutdown
- Enable Input
- Status Indication Fault Condition

- 5.5V LDO Mode Voltage Regulation
- Available in Space-Saving Small 8 Lead 2mm ×2mm SON

#### **APPLICATIONS**

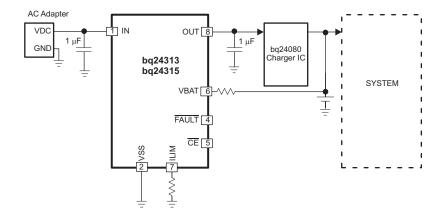
- Mobile Phones and Smart Phones
- PDAs
- MP3 Players
- Low-Power Handheld Devices
- Bluetooth™ Headsets

### **DESCRIPTION**

The bq24313 and bq24315 are highly integrated circuits designed to provide protection to Li-ion batteries from failures of the charging circuit. The IC continuously monitors the input voltage, the input current, and the battery voltage. The output acts as a linear regulator. The output is regulated to  $V_{O(REG)}$  for inputs between  $V_{O(REG)}$  and the overvoltage threshold. If an input overvoltage condition occurs, the IC immediately removes power from the charging circuit by turning off an internal switch. In the case of an overcurrent condition, it limits the system current at the threshold value, and if the overcurrent persists, switches the pass element OFF after a blanking period. Additionally, the IC also monitors its own die temperature and switches off if it exceeds 140°C. The input overcurrent threshold is user-programmable.

The IC can be controlled by a processor and also provides status information about fault conditions to the host.

#### **APPLICATION SCHEMATIC**



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PowerPAD is a trademark of Texas Instruments. Bluetooth is a trademark of Bluetooth SIG, Inc.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### ORDERING INFORMATION<sup>(1)</sup>

DEVICE <sup>(2)</sup>	OVP THRESHOLD	PACKAGE	MARKING
bq24313DSG	10.5V	2mm x 2mm SON	NXQ
bq24315DSG	5.85 V	2mm x 2mm SON	CGM

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (2) To order a 3000 piece reel add R to the part number, or to order a 250 piece reel add T to the part number.

#### PACKAGE DISSIPATION RATINGS

DESIGNATOR	PACKAGE	$R_{ heta$ JC	$R_{ hetaJA}$
DSG	2×2 SON	5°C/W	75°C/W

## **ABSOLUTE MAXIMUM RATINGS**(1)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	PIN	VALUE	UNIT
		IN (with respect to VSS)	-0.3 to 30	
VI	Input voltage	OUT (with respect to VSS)	-0.3 to 12	V
		ILIM, FAULT, CE, VBAT (with respect to VSS)	-0.3 to 7	
l <sub>l</sub>	Input current	IN	2	Α
lo	Output current	OUT	2	Α
	Output sink current	FAULT	15	mA
		All (Human Body Model per JESD22-A114-E)	2000	V
		All (Machine Model per JESD22-A115-E)	200	V
ESD	Withstand Voltage	All (Charge Device Model per JESD22-C101-C)		V
		IN(IEC 61000-4-2) (with IN bypassed to the VSS with a 1-μF low-ESR ceramic capacitor)	15 (Air Discharge) 8 (Contact)	kV
TJ	Junction temperature		-40 to 150	°C
T <sub>stg</sub>	Storage temperature		-65 to 150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. All voltage values are with respect to the network ground terminal unless otherwise noted.

#### RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V <sub>IN</sub>	Input voltage range	3.3	30	V
I <sub>IN</sub>	Input current, IN pin		1.5	Α
I <sub>OUT</sub>	Output current, OUT pin		1.5	Α
R <sub>(ILIM)</sub>	OCP Programming resistor	15	90	kΩ
TJ	Junction temperature	-40	125	°C

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## **ELECTRICAL CHARACTERISTICS**

over junction temperature range -40°C to 125°C and recommended supply voltage (unless otherwise noted)

	PARAMETER	TEST CONDI	TIONS	MIN	TYP	MAX	UNIT
IN							
UVLO	Undervoltage lock-out, input power detected threshold	CE = Low, V <sub>IN</sub> increasing from 0V to 3V			2.7	2.8	V
V <sub>hys(UVLO)</sub>	Hysteresis on UVLO	CE = Low, V <sub>IN</sub> decreasing from	200	260	300	mV	
t <sub>DGL(PGOOD)</sub>	Deglitch time, input power detected status	CE = Low. Time measured from rise-time, to output turning ON			8		ms
I <sub>DD</sub>	Operating current	$\overline{\text{CE}}$ = Low, No load on OUT p V <sub>IN</sub> = 5V, R <sub>(ILIM)</sub> = 25kΩ	in,		400	600	μΑ
I <sub>STDBY</sub>	Standby current	CE = High, V <sub>IN</sub> = 5V			65	95	μΑ
INPUT TO O	OUTPUT CHARACTERISTICS	1	,		-		
$V_{DO}$	Drop-out voltage IN to OUT	$\overline{CE}$ = Low, $V_{IN}$ = 5V, $I_{OUT}$ = 1/	4		170	280	mV
	TAGE REGULATION	1	<u> </u>				
$V_{O(REG)}$	Output voltage	$\overline{\text{CE}}$ = Low, $V_{\text{IN}}$ = 6.5V, $I_{\text{OUT}}$ = 1A	bq24313	5.67	5.85	6.03	V
		$\overline{\text{CE}}$ = Low, V <sub>IN</sub> = 5.7V, I <sub>OUT</sub> = 1A	bq24315	5.3	5.5	5.7	
INPUT OVE	RVOLTAGE PROTECTION						
1/	land and the same	CE = Low, V <sub>IN</sub> increasing	bq24313	10.2	10.5	10.8	
$V_{OVP}$	Input overvoltage protection threshold	from 5V to 11V	bq24315	5.71	5.85	6.00	V
t <sub>PD(OVP)</sub>	Input OV propagation delay <sup>(1)</sup>	CE = Low			200		ns
	Hysteresis on OVP	CE = Low, V <sub>IN</sub> decreasing	bq24313	60	120	180	
$V_{hys(OVP)}$	•	from 11V to 5V	bq24315	20	60	110	mV
t <sub>ON(OVP)</sub>	Recovery time from input overvoltage condition	$\overline{\text{CE}}$ = Low, Time measured from $V_{\text{IN}}$ 7.5V $\rightarrow$ 5V, 1 $\mu$ s fall-time			8		ms
INPUT OVE	RCURRENT PROTECTION	,	L				
	Input overcurrent protection threshold			200		4500	A
I <sub>OCP</sub>	range			300		1500	mA
I <sub>OCP</sub>	Input overcurrent protection threshold	$\overline{\text{CE}} = \text{Low}, \ \text{R}_{(\text{ILIM})} = 24.9 \text{k}\Omega, \\ 3 \ \text{V} \leq \text{V}_{\text{IN}} < \text{V}_{\text{OVP}} - \text{V}_{\text{hys}(\text{OVP})}$		900	1000	1100	mA
$K_{(ILIM)}$	Adjustable current limit factor				25		A = kΩ
$t_{BLANK(OCP)}$	Blanking time, input overcurrent detected				176		μs
t <sub>REC(OCP)</sub>	Recovery time from input overcurrent condition				64		ms
BATTERY O	VERVOLTAGE PROTECTION						
$BV_OVP$	Battery overvoltage protection threshold	$\overline{\text{CE}} = \text{Low},  \text{V}_{\text{IN}} > 4.4 \text{V}$		4.30	4.35	4.4	V
V <sub>hys(Bovp)</sub>	Hysteresis on BV <sub>OVP</sub>	$\overline{\text{CE}} = \text{Low},  \text{V}_{\text{IN}} > 4.4 \text{V}$		200	275	320	mV
I <sub>(VBAT)</sub>	Input bias current on VBAT pin	$V_{(VBAT)} = 4.4V, T_J = 25^{\circ}C$				10	nA
t <sub>DGL(Bovp)</sub>	Deglitch time, battery overvoltage detected	CE = Low, V <sub>IN</sub> > 4.4V. Time n rising from 4.1V to 4.4V to FA			176		μs
THERMAL F	PROTECTION						
T <sub>J(OFF)</sub>	Thermal shutdown temperature				140	150	°C
T <sub>J(OFF-HYS)</sub>	Thermal shutdown hysteresis				20		°C
LOGIC LEVI	ELS ON CE	1					
V <sub>IL</sub>	Low-level input voltage			0		0.4	V
V <sub>IH</sub>	High-level input voltage			1.4			V
I <sub>IL</sub>	Low-level input current	V <sub>(/CE)</sub> = 0V				1	μΑ

<sup>(1)</sup> Not tested in production. Specified by design.



## **ELECTRICAL CHARACTERISTICS (continued)**

over junction temperature range -40°C to 125°C and recommended supply voltage (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I <sub>IH</sub>	High-level input current	V <sub>(/CE)</sub> = 1.8V			15	μΑ
LOGIC	LEVELS ON FAULT					
$V_{OL}$	Output low voltage	I <sub>SINK</sub> = 5mA			0.2	V
I <sub>lkg</sub>	Leakage current, FAULT pin HI-Z	$V_{(/FAULT)} = 5V$			10	μΑ



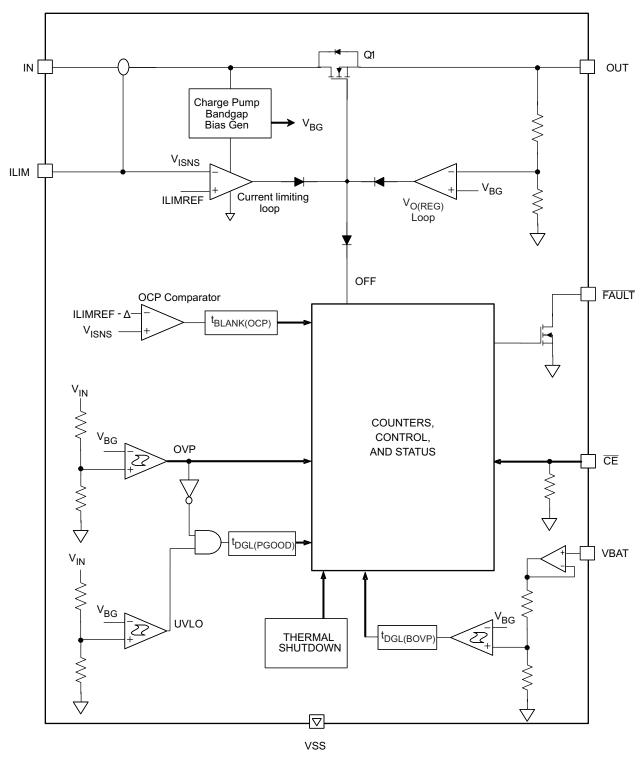


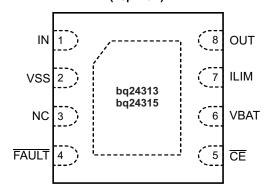
Figure 1. Simplified Block Diagram



### **TERMINAL FUNCTIONS**

TERMINAL			DECORPORTION
NAME	DSG	1/0	DESCRIPTION
IN	1	ı	Input power. Connect IN to the external DC supply. Bypass IN to VSS with a $1\mu F$ ceramic capacitor (minimum).
VSS	2	_	Ground terminal
NC	3		This pin may have internal circuits used for test purposes. Do not make any external connection to this pin for normal operation.
FAULT	4	0	Open-drain, device status output. FAULT = Low indicates that the input FET Q1 is off due to input overvoltage, input overcurrent, battery overvoltage, or thermal shutdown. FAULT is high impedance during normal operation. Connect a pullup resistor from FAULT to the desired logic level voltage rail.
CE	5	I	Chip enable active low input. Connect $\overline{CE}$ = High to disable the IC and turn the input FET off. Connect $\overline{CE}$ = low for normal operation. $\overline{CE}$ is internally pulled down.
VBAT	6	I	Battery voltage sense input. Connect to the battery pack positive terminal through a resistor.
ILIM	7	I/O	Input overcurrent threshold programming. Connect a resistor from ILIM to VSS to set the overcurrent threshold.
OUT	8	0	Output terminal to the charging system. Connect OUT to the external load circuitry. Bypass OUT to VSS with a $1\mu F$ ceramic capacitor (minimum).
Thermal PAD		_	There is an internal electrical connection between the exposed thermal pad and the VSS pin of the device. The thermal pad must be connected to the same potential as the VSS pin on the printed circuit board. Do not use the thermal pad as the primary ground input for the device. The VSS pin must be connected to ground at all times.

## DSG Package (Top View)





#### TYPICAL OPERATING PERFORMANCE

Test conditions (unless otherwise noted) for typical operating performance:  $V_{IN}=5$  V,  $C_{IN}=1$   $\mu F$ ,  $C_{OUT}=1$   $\mu F$ ,  $R_{(ILIM)}=25$  k $\Omega$ ,  $R_{BAT}=100$  k $\Omega$ ,  $T_A=25$ °C,  $V_{PU}=3.3$ V (see Figure 22 for the Typical Application Circuit)

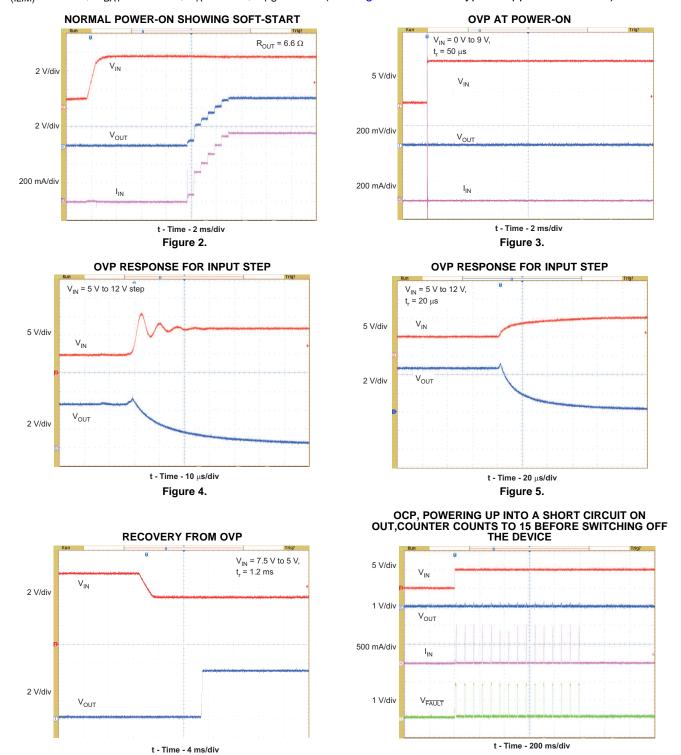
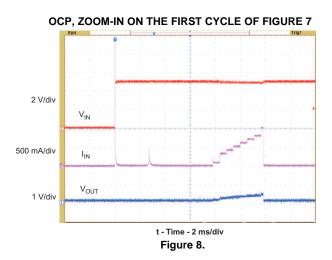


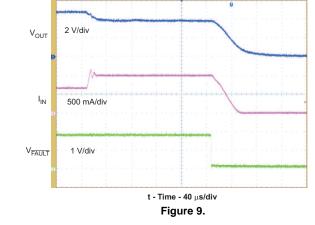
Figure 6.

Figure 7.

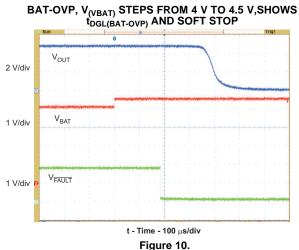


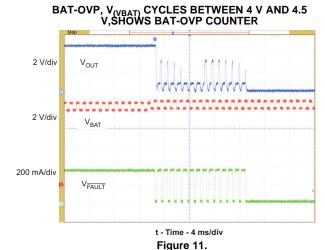
## **TYPICAL OPERATING PERFORMANCE (continued)**

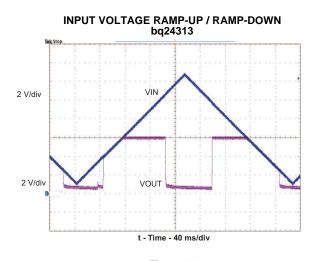




 $R_{OUT}$  SWITCHES FROM  $6.6\Omega$  TO  $3.3\Omega,\!SHOWS$  CURRENT LIMITING AND SOFT-STOP







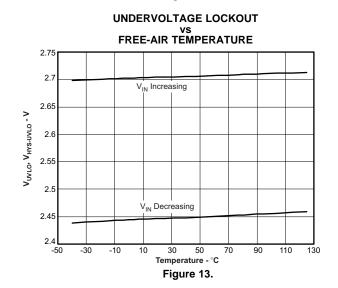


Figure 12.



## **TYPICAL OPERATING PERFORMANCE (continued)**

10.4

10.35

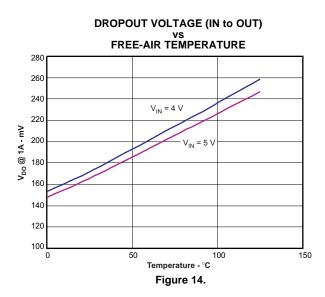
10.3

-50

-30

-10

10



# bq24313 10.55 V<sub>IN</sub> Increasing 10.5 VovP, VHYS-OVP - V 10.45

**OVERVOLTAGE PROTECTION THRESHOLD** 

vs FREE-AIR TEMPERATURE

30 50 Temperature °C Figure 15.

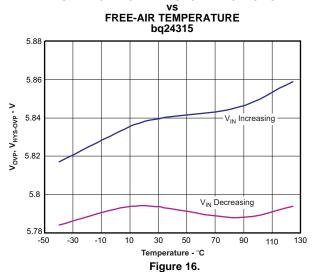
90

110

130

V<sub>IN</sub> Decreasing

# **OVERVOLTAGE THRESHOLD PROTECTION**



#### INPUT OVERCURRENT PROTECTION

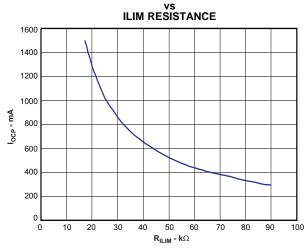
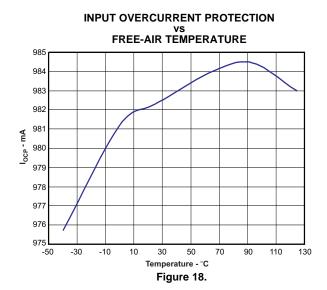


Figure 17.

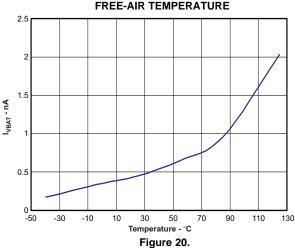


## **TYPICAL OPERATING PERFORMANCE (continued)**



## BATTERY OVERVOLTAGE PROTECTION vs FREE-AIR TEMPERATURE 4.35 BV<sub>OVP</sub> (V<sub>VBAT</sub> Increasing) 4.3 4.25 4.2 4.15 Bat-OVP Recovery ( $V_{VBAT}$ Decreasing) 4.1 4.05 -30 -50 -10 50 110 130 Temperature - °C

# LEAKAGE CURRENT (VBAT Pin) vs FREE-AIR TEMPERATURE



#### SUPPLY CURRENT vs INPUT VOLTAGE

Figure 19.

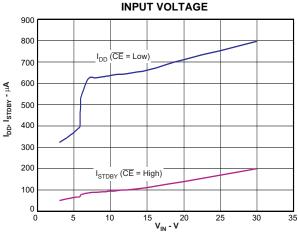


Figure 21.



#### TYPICAL APPLICATION CIRCUIT

 $V_{OVP} = 5.85V$ ,  $I_{OCP} = 1000mA$ ,  $BV_{OVP} = 4.35V$ 

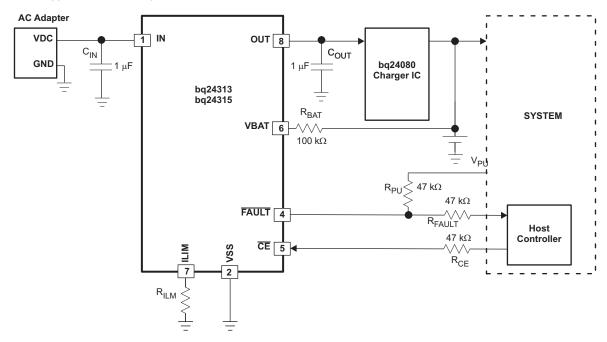


Figure 22.

#### **DETAILED FUNCTIONAL DESCRIPTION**

The bq24313 and bq24315 are integrated circuits designed to provide protection to Li-ion batteries from failures of the charging circuit. The IC continuously monitors the input voltage, the input current and the battery voltage. For an input overvoltage condition, the IC immediately removes power from the charging circuit by turning off an internal switch. For an overcurrent condition, it limits the system current at the threshold value, and if the overcurrent persists, switches the pass element OFF after a blanking period. If the battery voltage rises to an unsafe level, the IC disconnects power from the charging circuit until the battery voltage returns to an acceptable value. Additionally, the IC also monitors its own die temperature and switches off if it exceeds 140°C. The input overcurrent threshold is user-programmable. The IC can be controlled by a processor, and also provides status information about fault conditions to the host.

#### **POWER DOWN**

The device remains in power down mode when the input voltage at the IN pin is below the undervoltage threshold UVLO. The FET Q1 connected between IN and OUT pins is off, and the status output, FAULT, is set to Hi-Z.

#### **POWER-ON RESET**

The device resets when the input voltage at the IN pin exceeds the UVLO threshold. All internal counters and other circuit blocks are reset. The IC then waits for duration  $t_{DGL(PGOOD)}$  for the input voltage to stabilize. If, after  $t_{DGL(PGOOD)}$ , the input voltage and battery voltage are safe, FET Q1 is turned ON. The IC has a soft-start feature to control the inrush current. The soft-start minimizes the ringing at the input (the ringing occurs because the parasitic inductance of the adapter cable and the input bypass capacitor form a resonant circuit). Because of the deglitch time at power-on, if the input voltage rises rapidly to beyond the OVP threshold, the device will not switch on at all, instead it will go into protection mode and indicate a fault on the FAULT pin.

#### **OPERATION**

The device continuously monitors the input voltage, the input current, and the battery voltage as described in detail in the following sections.



#### **Input Overvoltage Protection**

While the input voltage is less than  $V_{O(REG)}$ , the output voltage tracks the input voltage (less the drop due to the  $R_{DS(on)}$  of Q1). When the input voltage is between  $V_{O(REG)}$  and  $V_{OVP}$ , the device functions as a linear regulator and regulates the output voltage to 5.5V. If the input voltage rises above  $V_{OVP}$ , the internal FET Q1 is turned off, removing power to the output. The response is rapid, with the FET turning off in less than a microsecond. The FAULT pin is driven low. When the input voltage returns below  $V_{OVP} - V_{hys(OVP)}$  (but is still above UVLO), the FET Q1 is turned on again after a deglitch time of  $t_{ON(OVP)}$  to ensure that the input supply has stabilized.

#### **Input Overcurrent Protection**

The overcurrent threshold is programmed by a resistor  $R_{(ILIM)}$  connected from the ILIM pin to VSS. Figure 17 shows the OCP threshold as a function of  $R_{(ILIM)}$ , and may be approximated by the following equation:  $I_{OCP} = 25 \div R_{(ILIM)}$  (current in A, resistance in  $k\Omega$ )

If the load current tries to exceed the  $I_{OCP}$  threshold, the device limits the current for a blanking duration of  $t_{BLANK(OCP)}$ . If the load current returns to less than  $I_{OCP}$  before  $t_{BLANK(OCP)}$  times out, the device continues to operate. However, if the overcurrent situation persists for  $t_{BLANK(OCP)}$ , the FET Q1 is turned off for a duration of  $t_{REC(OCP)}$ , and the FAULT pin is driven low. The FET is then turned on again after  $t_{REC(OCP)}$  and the current is monitored all over again. Each time an OCP fault occurs, an internal counter is incremented. If 15 OCP faults occur in one charge cycle, the FET is turned off permanently. The counter is cleared either by removing and re-applying input power, or by disabling and re-enabling the device with the  $\overline{CE}$  pin.

To prevent the input voltage from spiking up due to the inductance of the input cable, Q1 is turned off slowly, resulting in a "soft-stop".

#### **Battery Overvoltage Protection**

The battery overvoltage threshold  $BV_{OVP}$  is internally set to 4.35V. If the battery voltage exceeds the  $BV_{OVP}$  threshold, the FET Q1 is turned off, and the FAULT pin is driven low. The FET is turned back on once the battery voltage drops to  $BV_{OVP} - V_{hys(Bovp)}$ . Each time a battery overvoltage fault occurs, an internal counter is incremented. If 15 such faults occur in one charge cycle, the FET is turned off permanently. The counter is cleared either by removing and re-applying input power, or by disabling and re-enabling the device with the CE pin. For a battery overvoltage fault, Q1 is gradually switched OFF.

#### **Thermal Protection**

If the junction temperature of the device exceeds  $T_{J(OFF)}$ , the FET Q1 is turned off, and the  $\overline{FAULT}$  pin is driven low. The FET is turned back on when the junction temperature falls below  $T_{J(OFF)} - T_{J(OFF-HYS)}$ .

#### **Enable Function**

The IC has an enable pin which can be used to enable or disable the device. When the CE pin is driven high, the internal FET is turned off. When the CE pin is low, the FET is turned on if other conditions are safe. The OCP counter and the Bat-OVP counter are both reset when the device is disabled and re-enabled. The CE pin has an internal pulldown resistor and can be left floating. Note that the FAULT pin functionality is also disabled when the CE pin is high.

#### **Fault Indication**

The FAULT pin is an active-low open-drain output. It is in a high-impedance state when operating conditions are safe, or when the device is disabled by setting CE high. With CE low, the FAULT pin goes low whenever any of these events occurs:

- Input overvoltage
- Input overcurrent
- Battery overvoltage
- IC Overtemperature



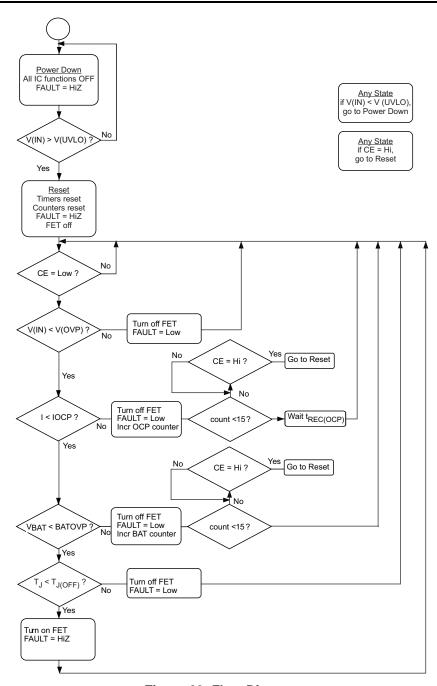


Figure 23. Flow Diagram



#### **APPLICATION INFORMATION (WITH REFERENCE TO FIGURE 22)**

## Selection of R<sub>BAT</sub>

It is strongly recommended that the battery not be tied directly to the VBAT pin of the device, as under some failure modes of the IC, the voltage at the IN pin may appear on the VBAT pin. This voltage can be as high as 30V, and applying 30V to the battery in case of the failure of the bq24315 can be hazardous. Connecting the VBAT pin through  $R_{BAT}$  prevents a large current from flowing into the battery in case of a failure of the IC. In the interests of safety,  $R_{BAT}$  should have a high value. The problem with a large  $R_{BAT}$  is that the voltage drop across this resistor, due to the VBAT bias current  $I_{(VBAT)}$ , causes an error in the  $BV_{OVP}$  threshold. This error is over and above the tolerance on the nominal 4.35V  $BV_{OVP}$  threshold.

Choosing  $R_{BAT}$  in the range  $100k\Omega$  to  $470k\Omega$  is a good compromise. In the event of an IC failure, with  $R_{BAT}$  equal to  $100k\Omega$ , the maximum current flowing into the battery would be  $(30V-3V)\div 100k\Omega=246\mu A$ , which is low enough to be absorbed by the bias currents of the system components.  $R_{BAT}$  equal to  $100k\Omega$  results in a worst-case voltage drop of  $R_{BAT}\times I_{(VBAT)}=1$ mV. This is negligible to compared to the internal tolerance of 50mV on  $BV_{OVP}$  threshold.

If the Bat-OVP function is not required, the VBAT pin should be connected to VSS.

#### Selection of R<sub>CE</sub>, R<sub>FAULT</sub>, and R<sub>PU</sub>

The  $\overline{\text{CE}}$  pin can be used to enable and disable the IC. If host control is not required, the  $\overline{\text{CE}}$  pin can be tied to ground or left un-connected, permanently enabling the device.

In applications where external control is <u>required</u>, the CE pin can be controlled by a host processor. As in the case of the VBAT pin (see above), the  $\overline{\text{CE}}$  pin should be connected to the host GPIO pin through as large a resistor as possible. The limitation on the resistor value is that the <u>minimum V<sub>OH</sub></u> of the host GPIO pin less the drop across the resistor should be greater than V<sub>IH</sub> of the bq24315  $\overline{\text{CE}}$  pin. The drop across the resistor is given by R<sub>CE</sub> × I<sub>IH</sub>.

The  $\overline{\text{FAULT}}$  pin is an open-drain output that goes low during OV, OC, battery-OV, and  $\overline{\text{OT}}$  events. If the application does not require monitoring of the  $\overline{\text{FAULT}}$  pin, it can be left unconnected. But if the  $\overline{\text{FAULT}}$  pin has to be monitored, it should be pulled high externally through  $R_{\text{PU}}$ , and connected to the host through  $R_{\text{FAULT}}$ .  $R_{\text{FAULT}}$  prevents damage to the host controller if the bq24315 fails (see above). The resistors should be of high value, in practice values between  $22k\Omega$  and  $100k\Omega$  should be sufficient.

#### Selection of Input and Output Bypass Capacitors

The input capacitor  $C_{IN}$  in Figure 22 is for decoupling, and serves an important purpose. Whenever there is a step change downwards in the system load current, the inductance of the input cable causes the input voltage to spike up.  $C_{IN}$  prevents the input voltage from overshooting to dangerous levels. It is recommended that a ceramic capacitor of at least  $1\mu F$  be used at the input of the device. It should be located in close proximity to the IN pin.

 $C_{\text{OUT}}$  in Figure 22 is also important: If a fast (< 1 $\mu$ s rise time) overvoltage transient occurs at the input, the current that charges  $C_{\text{OUT}}$  causes the device's current-limiting loop to start, reducing the gate-drive to FET Q1. This results in improved performance for input overvoltage protection.  $C_{\text{OUT}}$  should also be a ceramic capacitor of at least 1 $\mu$ F, located close to the OUT pin.  $C_{\text{OUT}}$  also serves as the input decoupling capacitor for the charging circuit downstream of the protection IC.

#### **Powering Accessories**

In some applications, the equipment that the protection IC resides in may be required to provide power to an accessory (e.g. a cellphone may power a headset or an external memory card) through the same connector pins that are used by the adapter for charging. Figure 24 and Figure 25 illustrate typical charging and accessory-powering scenarios:



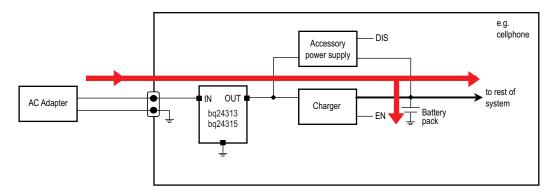


Figure 24. Charging - The Red Arrows Show the Direction of Current Flow

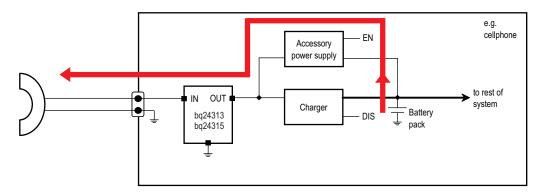


Figure 25. Powering an Accessory - The Red Arrows Show the Direction of Current Flow

In the second case, when power is being delivered to an accessory, the bq24313/bq24315 device is required to support current flow from the OUT pin to the IN pin.

If  $V_{OUT} > UVLO + 0.7V$ , FET Q1 is turned on, and the reverse current does not flow through the diode but through Q1. Q1 remains ON as long as  $V_{OUT} > UVLO - V_{hys(UVLO)} + R_{DS(on)} \times I_{(ACCESSORY)}$ . Within this voltage range, the reverse current capability is the same as the forward capability, 1.5A. It should be noted that there is no overcurrent protection in this direction.

#### **PCB Layout Guidelines:**

- This device is a protection device, and is meant to protect down-stream circuitry from hazardous voltages.
   Potentially, high voltages may be applied to this IC. It has to be ensured that the edge-to-edge clearances of PCB traces satisfy the design rules for high voltages.
- The device uses SON packages with a PowerPAD™. For good thermal performance, the PowerPAD should be thermally coupled with the PCB ground plane. In most applications, this will require a copper pad directly under the IC. This copper pad should be connected to the ground plane with an array of thermal vias.
- C<sub>IN</sub> and C<sub>OUT</sub> should be located close to the IC. Other components like R<sub>(ILIM)</sub> and R<sub>BAT</sub> should also be located close to the IC.





10-Jun-2014

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
BQ24313DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	NXQ	Samples
BQ24313DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	NXQ	Samples
BQ24315DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CGM	Samples
BQ24315DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CGM	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.



## PACKAGE OPTION ADDENDUM

10-Jun-2014

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## PACKAGE MATERIALS INFORMATION

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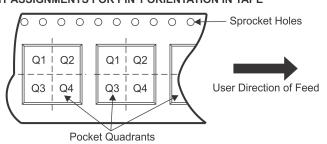
## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ24313DSGR	WSON	DSG	8	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
BQ24313DSGR	WSON	DSG	8	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
BQ24313DSGT	WSON	DSG	8	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
BQ24313DSGT	WSON	DSG	8	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
BQ24315DSGR	WSON	DSG	8	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
BQ24315DSGR	WSON	DSG	8	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
BQ24315DSGT	WSON	DSG	8	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
BQ24315DSGT	WSON	DSG	8	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2

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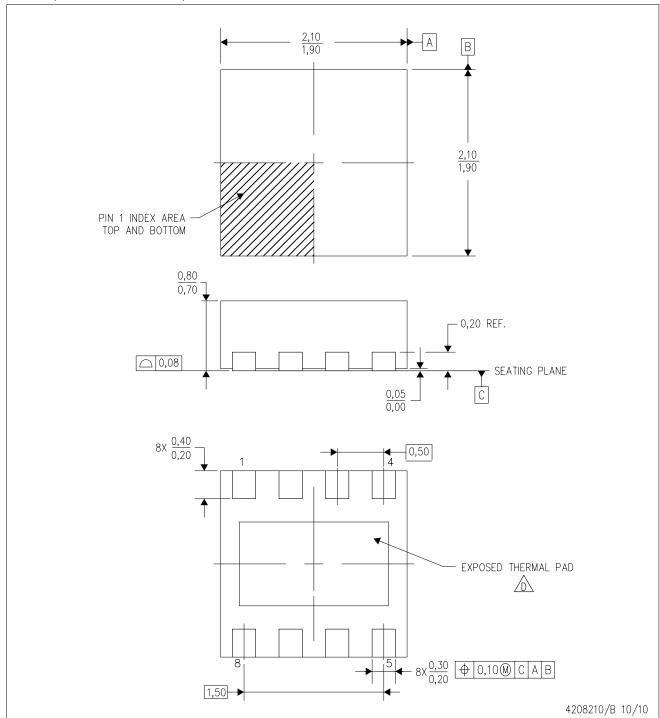


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ24313DSGR	WSON	DSG	8	3000	205.0	200.0	33.0
BQ24313DSGR	WSON	DSG	8	3000	195.0	200.0	45.0
BQ24313DSGT	WSON	DSG	8	250	205.0	200.0	33.0
BQ24313DSGT	WSON	DSG	8	250	195.0	200.0	45.0
BQ24315DSGR	WSON	DSG	8	3000	195.0	200.0	45.0
BQ24315DSGR	WSON	DSG	8	3000	205.0	200.0	33.0
BQ24315DSGT	WSON	DSG	8	250	205.0	200.0	33.0
BQ24315DSGT	WSON	DSG	8	250	195.0	200.0	45.0

DSG (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- This drawing is subject to change without notice.
- Quad Flatpack, No-Leads (QFN) package configuration.
- The package thermal pad must be soldered to the board for thermal and mechanical performance.

See the Product Data Sheet for details regarding the exposed thermal pad dimensions.

E. Falls within JEDEC MO-229.



## DSG (S-PWSON-N8)

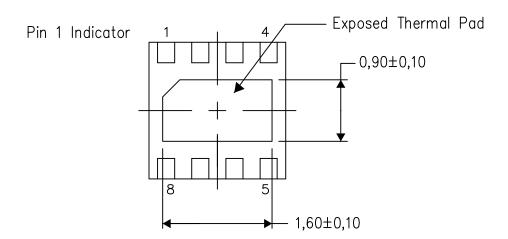
PLASTIC SMALL OUTLINE NO-LEAD

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

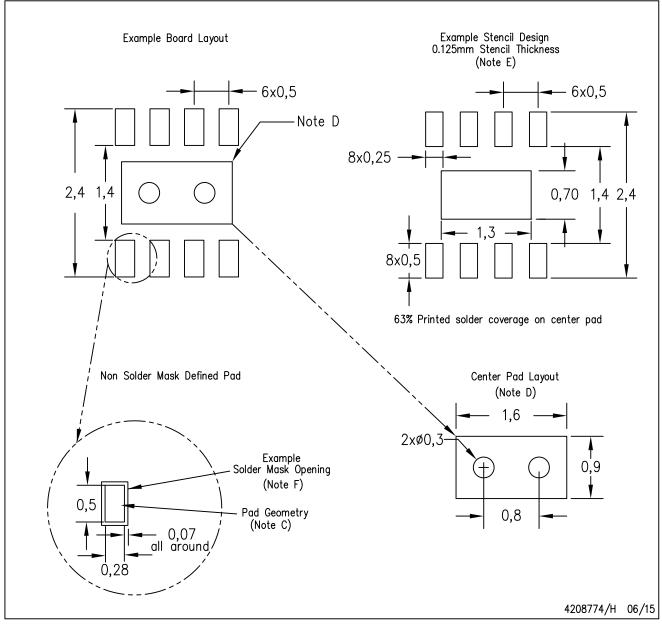
4208347/I 06/15

NOTE: All linear dimensions are in millimeters



## DSG (S-PWSON-N8)

## PLASTIC SMALL OUTLINE NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for solder mask tolerances.



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